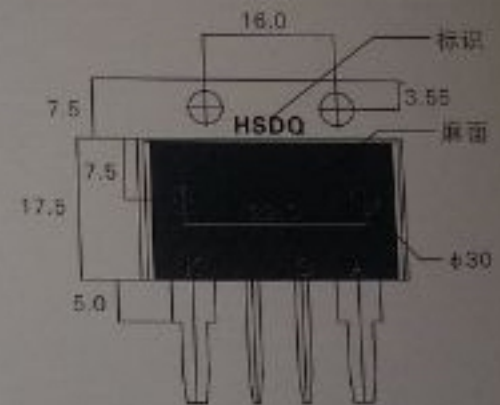
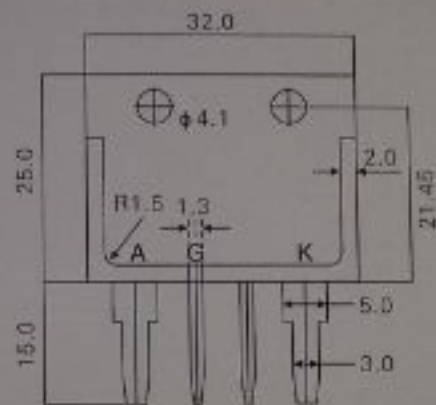
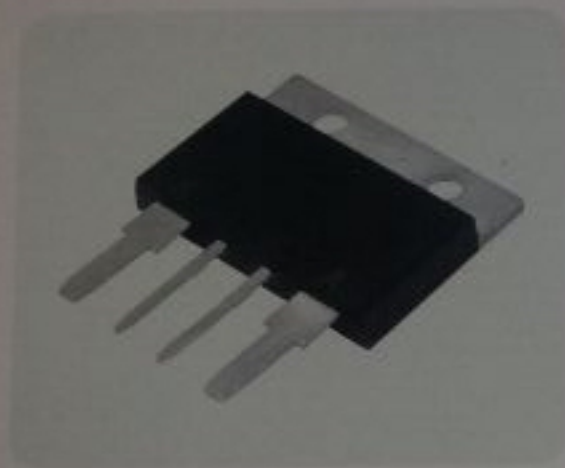


# 功率半导体器件



## BT80双向可控硅

**特点:** 先进的玻璃钝化工艺, 灵敏的控制极触发电流, 较低的通态压降, 通过ROHS认证。

**用途:** 用于各种万能开关器、小型马达控制器、彩灯控制器、漏电保护器、逻辑集成电路驱动、摩托车点火器等电路中。

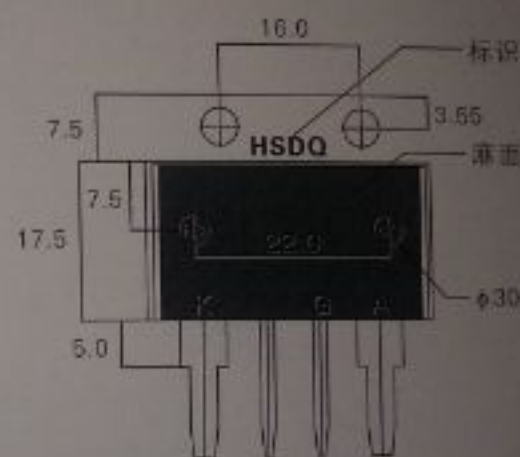
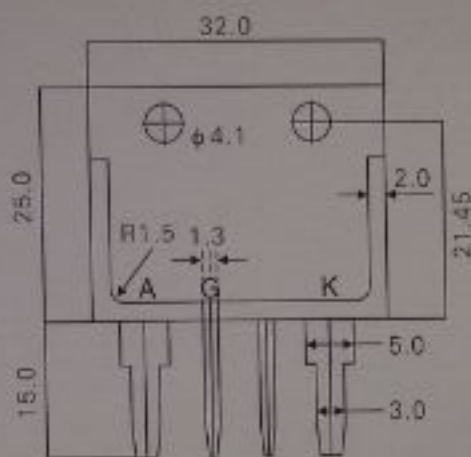
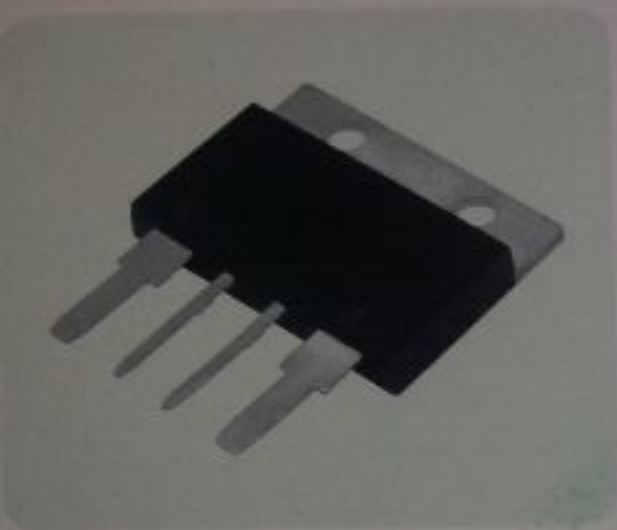
### 极限值

参数名称	符号	规范值	单位
断态重复峰值断电压	$V_{DRM}$	$\geq 800$	V
反向重复峰值断电压	$V_{RRM}$	$\geq 800$	V
通态方均根电流	$I_{T(RMS)}$	80	A
通态浪涌电流	$I_{TSM}$	800	A
工作结温	$T_j$	-40 ~ 125	$^{\circ}\text{C}$
贮存温度	$T_{stg}$	-40 ~ 150	$^{\circ}\text{C}$

### 电特性( $T_j=25^{\circ}\text{C}$ )

参数名称	符号	规范值	单位	测试条件
通态峰值电压	$V_{TM}$	1.50	V	$I_T=120\text{A}$
断态重复峰值电流	$I_{DRM}$	$\leq 1.5$	mA	$V_{DRM}=800\text{V}$
门极触发电流	T2+G+	$\leq 50$	mA	$V_{DRM}=12\text{V}$ $R_L=10\Omega$
	T2+G-	$\leq 50$		
	T2-G-	$\leq 50$		
	T2-G+	$\leq 80$		
门极触发电压	$V_{GT}$	$\leq 1.3$	V	$V_D=12\text{V}$ $R_L=10\Omega$
维持电流	$I_H$	80	mA	
断态电压临界上升率	$dv/dt$	$\geq 500$	V/ $\mu\text{S}$	

# Power semiconductor devices



## BT80 two-way controllable silicon

**Characteristics:** advanced glass passivated device, sensitive control pole triggering current, relatively low on-state voltage drop and passed ROHS certification.

**Purpose:** used in circuits of various motor speed controller, small-size motor controller, color light controller, leakage protector, driving of logic integrated circuit, etc.

### Limit value

Parameter name	Symbol	Normative value	Unit
Off-state repetitive peak blocking voltage	$V_{DRM}$	$\geq 800$	V
Reverse repetitive peak blocking voltage	$V_{RRM}$	$\geq 800$	V
On-state rms current	$I_{T(RMS)}$	80	A
On-state surging current	$I_{TM}$	800	A
Working junction temperature	$T_j$	-40 ~ 125	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-40 ~ 150	$^{\circ}\text{C}$

### Electric speciality ( $T_j=25^{\circ}\text{C}$ )

Parameter name	Symbol	Normative value	Unit	Test conditions
On-state peak voltage	$V_{TM}$	1.50	V	$I_T=120\text{A}$
Off-state repetitive peak current	$I_{DRM}$	$\leq 1.5$	mA	$V_{DRM}=800\text{V}$
Gate triggering current	$I_{GT}$	$\leq 50$	mA	$V_{AK}=12\text{V}$ $R_i=10\Omega$
		$\leq 50$		
		$\leq 50$		
		$\leq 80$		
Gate triggering voltage	$V_{GT}$	$\leq 1.3$	V	$V_{AK}=12\text{V}$ $R_i=10\Omega$
Maintaining current	$I_h$	80	mA	
Critical rising rate of off-state voltage	$dv/dt$	$\geq 500$	V/ $\mu\text{S}$	